

12 with a fluorescent material containing layer 21 applied to its back side. This light emitting diode element 20 is a blue light emitting element made of gallium nitride type compound semiconductor. As shown in Fig. 3, it has a structure in which an n-type semiconductor 23 and a p-type semiconductor 24 are grown on the top surface of a sapphire substrate 22. The n-type semiconductor 23 and the p-type semiconductor 24 are provided with electrodes 25 and 26, and connected to the topside electrodes 13 and 14 arranged on the above-mentioned glass epoxy substrate 12 with bonding wires 27 and 28 for blue luminescence.

IN THE CLAIMS

Cancel claims 1 and 3 without prejudice or disclaimer and enter the following new claims:

26. (New) A light emitting diode comprising:
a. a base;
b. a fluorescent material containing layer containing a fluorescent material provided on said base;
c. a light emitting diode element mounted on the fluorescent material containing layer; and
d. a resin seal member provided to lap a surface side of the light emitting diode member;
wherein the light emitting diode element is